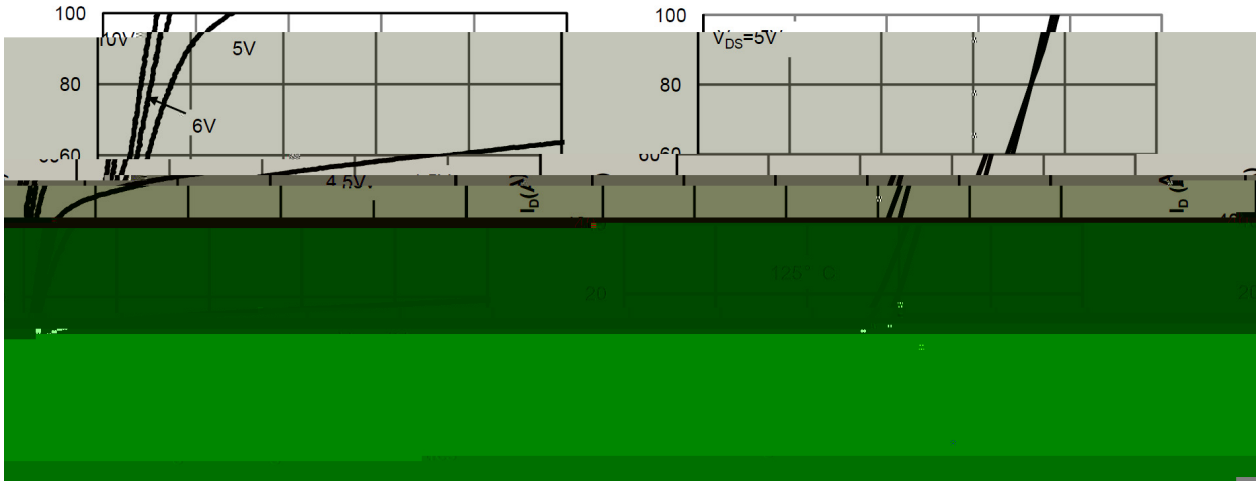
TO-263 N

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	80	V
Drain Current		I_D(Tc=25℃)	115	A
Pulsed Drain Current		I_{DM}	241	A
Gate-Source Voltage		V_{GS}	±20	V
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	710	mJ
Avalanche Current		I_{AS}	36.5	A
Total Power Dissipation		P_D(Tc=25℃)	156.2	W
Junction and Storage Temperature Range		T_J,T_{STG}	-55 to 150	
Thermal Resistance-Junction to Ambient	t≤10s	$R_{\theta JA}$	15.5	/W
	Steady-State		62.5	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.8	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	80	95		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=85V V_{GS}=0V			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	2	3	4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=20A		5.1	6.5	mΩ
	$R_{DS(on)}$	V_{GS}=6V I_D=10A		7.0	10	
Forward On Voltage	V_{SD}	V_{GS}=0V I_S=1A			1.2	V
Gate resistance	R_g	f=1MHz		1.4		Ω
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1MHz		3230		pF
Output Capacitance	C_{oss}			1310		
Reverse Transfer Capacitance	C_{rss}			185		
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V, V_{DS}=40V, I_D=20A		46		nC
Gate Source Charge	Q_{gs}			13		
Gate Drain Charge	Q_{gd}			8.5		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}				

/ Electrical Characteristic Curve



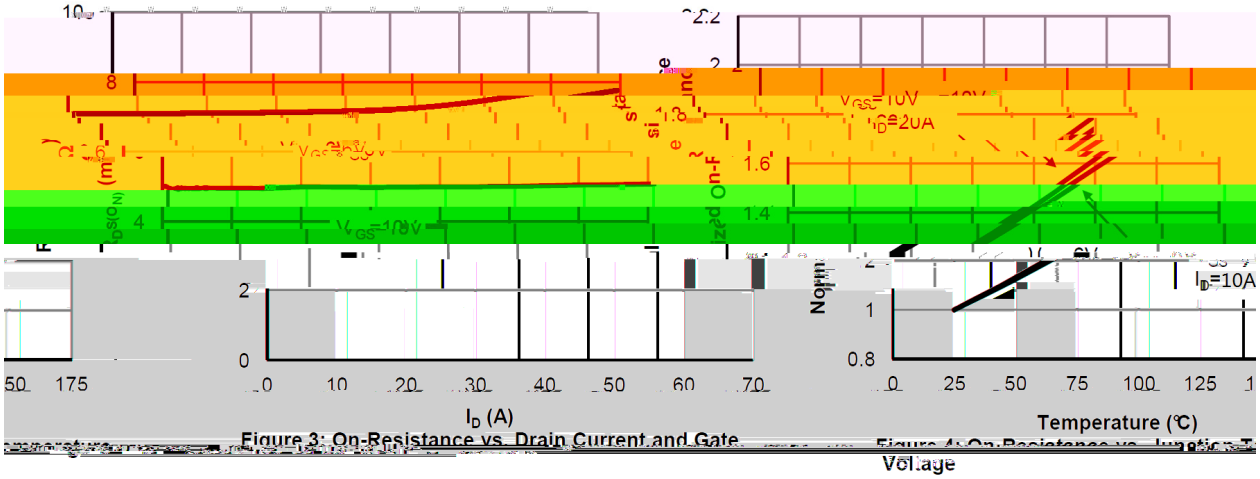
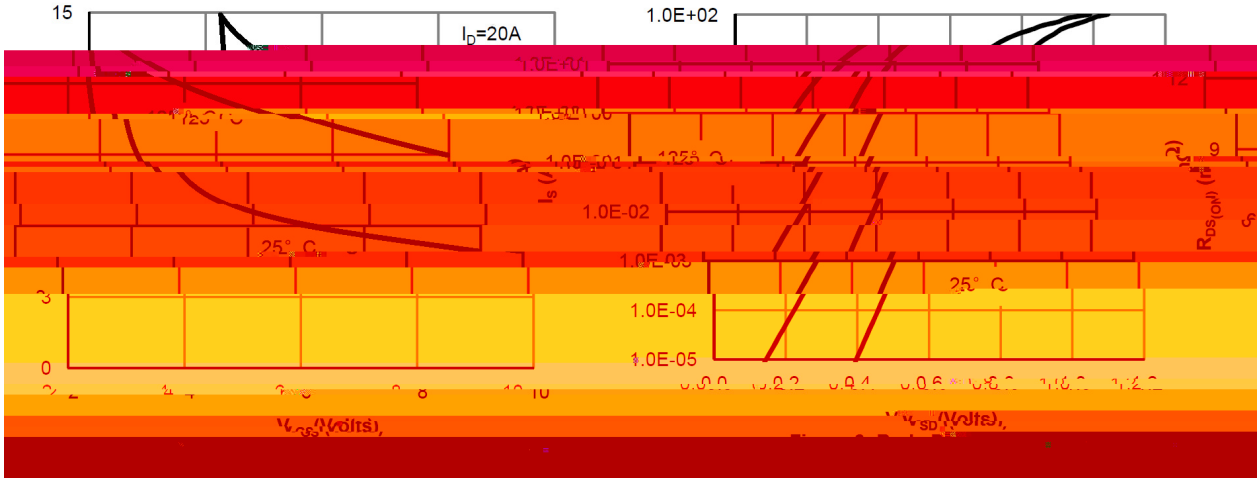
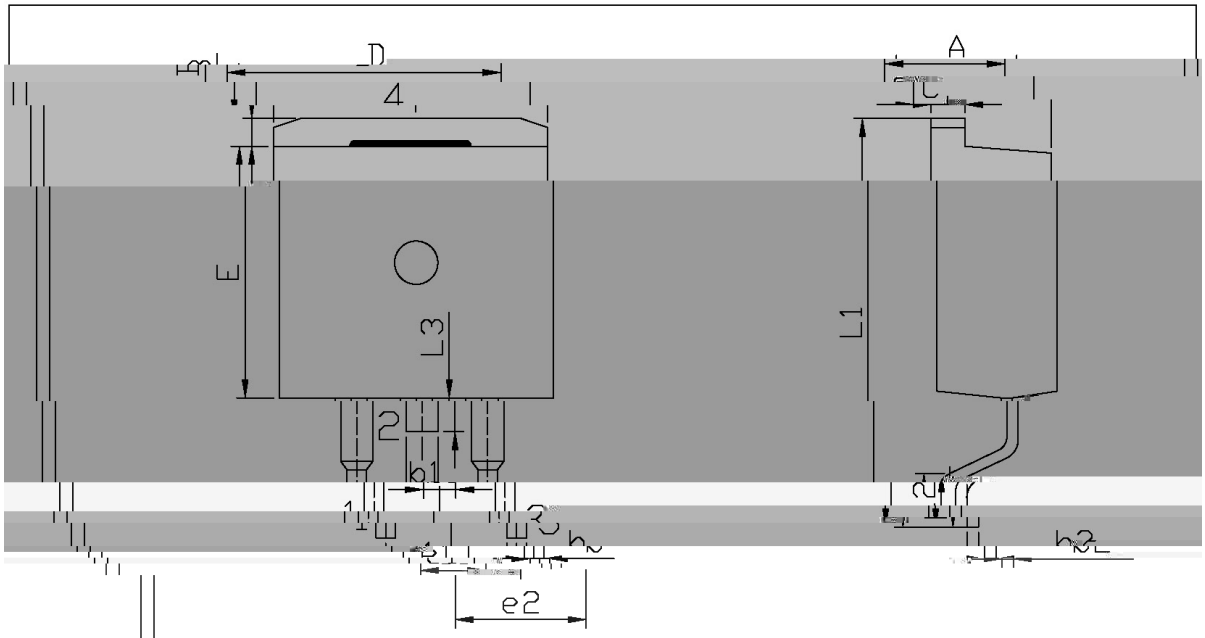


Figure 3: On-Resistance vs. Drain Current and Gate Voltage



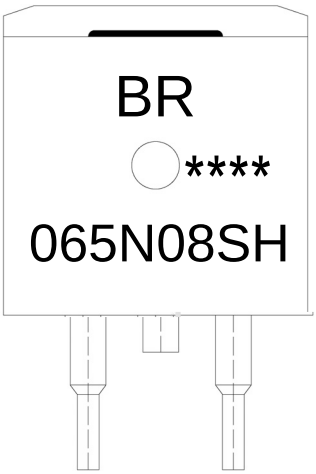
/ Package Dimensions



单位：m

Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.24	2.74

/ Marking Instructions



Note:

BR:	Company Code
065N08SH:	Product Type
****:	Lot No. Code, code change with Lot No